

RF Power Field Effect Transistors N-Channel Enhancement-Mode Lateral MOSFETs, MOSFET VHV6 300W TO272WB4N

Manufacturers	NXP Semiconductor
Package/Case	TO-272
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for MRF6V2300NBR1 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

MRF6V2300NBR1 is a part number for a high-power N-channel RF power field-effect transistor (FET) manufactured by NXP Semiconductors.

Features

Frequency range: 2300-2400 MHz

Output power: 300 W

Efficiency: 60%

Input power: 32.5 dBm

Drain-source voltage: 65 V

Package type: NI-780

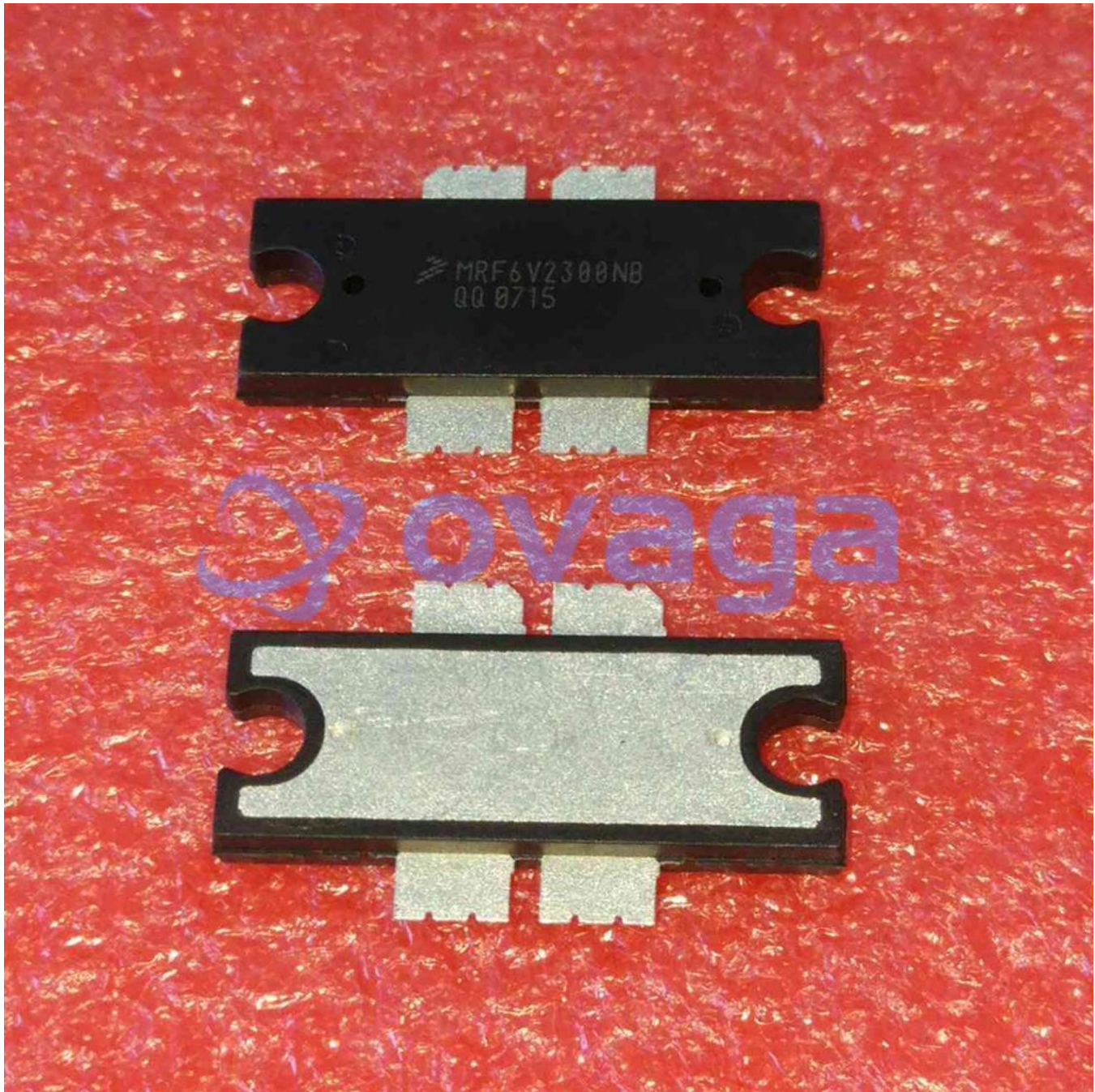
Application

MRF6V2300NR1: same part, but without gold plating on the leads

BLF6G24LS-230B: a similar N-channel RF power FET from NXP

MGFC36V5959A: an N-channel RF power FET from Mitsubishi Electric Semiconductor Division





Related Products



[MRFE6S9125NR1](#)

NXP Semiconductor
TO-270



[MRF6S20010GNR1](#)

NXP Semiconductor
TO-270



[MRF9030LR1](#)

NXP Semiconductor
NI-360-3



[MRF8P20100HSR3](#)

NXP Semiconductor
NI-780S-4



[MRF8P20160HSR3](#)

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NI-780S-4



[MRF6VP2600HR6](#)

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NI-1230



[MRF6VP2600H](#)

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SMD



[MRF374A](#)

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NI-650